NSN 5961-00-306-7232

Semiconductor Device Set - Page 1 of 1

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Inclosure Material:

Ceramic all transistor and metal all transistor

Overall Length:

0.725 inches all transistor

Mounting Facility Quantity:

2 all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

2 transistor

Mounting Method:

Unthreaded hole all transistor

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

70.0 breakdown voltage, collector-to-emitter, with base short-circuited to emitter all transistor

Current Rating Per Characteristic:

100.00 milliamperes source cutoff current all transistor

Power Rating Per Characteristic:

100.0 watts large-signal input power, common-emitter universal all transistor

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction all transistor

Test Data Document:

12338-44817-00 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

4 ribbon all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0